

Application No.: 10/771,566

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REMARKS

Claims 1-6 were pending in the present application. Claims 5-6 were withdrawn from consideration. By virtue of this response, claim 1 has been amended and claim 2 has been cancelled. No new claims have been added. Accordingly, claims 1, 3, and 4 are currently under consideration. Support for the amendment to claim 1 may be found in the present application, for example, on page 4, lines 14-32, page 5, lines 19-33, page 6, lines 12-25, and original claim 2. Accordingly, no new matter has been added. Amendment and cancellation of certain claims is not to be construed as a dedication to the public of any of the subject matter of the claims as previously presented.

Interview Summary

Applicants appreciated the opportunity to discuss the Office Action with the Examiner in the telephonic interview on July 6, 2005. In the interview, Applicant's attorney (Christopher B. Eide) discussed the content of the Office Action and cited references with reference to claim 1. No agreement was made as to any claim amendments. Additionally, the Examiner indicated that claim 6 was inadvertently left off of the "Office Action Summary" page and should have been included as withdrawn.

Rejections under 35 U.S.C. §102(e)

Claims 1, 2, and 4 stand rejected as being anticipated by Huang et al., U.S. Patent No. 6,693,352 (hereinafter, "Huang").

Applicants have amended claim 1 to recite an electrode employing a nitride-based semiconductor of III-V group compound, comprising a nitride-based semiconductor layer of III-V group compound, an electrode metal, a metal oxide inserted between said nitride-based semiconductor layer of III-V group compound and said electrode metal, and "a nitride semiconductor intermediate layer doped with oxygen, said nitride semiconductor intermediate layer

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formed during a heating process from said metal oxide and said nitride-based semiconductor layer of III-V group compound between said electrode metal and the underlying nitride based semiconductor layer of III-V group compound." Applicants submit that Huang fails to disclose or suggest the above recited features. In particular, Huang fails to disclose or suggest "a nitride semiconductor intermediate layer doped with oxygen," as recited by claim 1.

Huang discloses a metal pad layer 38A disposed over a conducting oxide layer 37A, which is in turn disposed over a p+-type layer 35 (see, e.g., Fig. 7 and Col. 5, lines 23-61). There is no disclosure or suggestion of a nitride semiconductor intermediate layer disposed between the metal oxide layer and the nitride-based semiconductor layer as presently recited by claim 1. Moreover, Huang does not disclose a manufacturing process similar to the heating process described in the present application after a lamination that would suggest a nitride semiconductor intermediate layer is present in the device/structure of Huang.

Accordingly, for at least these reasons Huang fails to disclose or suggest the features of the present claims and the rejection should be withdrawn. Claim 1 (and claims 3 and 4, which depend from claim 1) are therefore in condition for allowance.

Rejections under 35 U.S.C. §103(a)

Claim 3 stands rejected as allegedly being unpatentable over Huang in view of Steekl et al. (U.S. Patent No. Application 2003/0230970).

Claim 3 depends from claim 1 and is allowable over Huang for at least similar reasons as claim 1. The addition of Steekl et al. fails to cure the deficiencies of Huang discussed above, nor is it alleged to cure the deficiencies of Huang. Accordingly, the rejection should be withdrawn and claim 3 allowed.

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CONCLUSION

In view of the above, each of the presently pending claims in this application is believed to be in immediate condition for allowance. Accordingly, the Examiner is respectfully requested to withdraw the outstanding rejection of the claims and to pass this application to issue. If it is determined that a telephone conference would expedite the prosecution of this application, the Examiner is invited to telephone the undersigned at the number given below.

In the event the U.S. Patent and Trademark office determines that an extension and/or other relief is required, applicant petitions for any required relief including extensions of time and authorizes the Commissioner to charge the cost of such petitions and/or other fees due in connection with the filing of this document to Deposit Account No. 03-1952 referencing docket no. 245402008300. However, the Commissioner is not authorized to charge the cost of the issue fee to the Deposit Account.

Dated: July 19, 2005

Respectfully submitted,

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